Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1. (Currently Amended) An apparatus for processing a substrate with a plasma, the apparatus comprising:
 - a first electrode:
- a second electrode having a parallel plate arrangement with said first electrode movable relative to said first electrode between a first position to define a processing region for the substrate between said first electrode and said second electrode and a second position for transferring the substrate to and from said processing region;
- a <u>tubular</u> separating [[ring]] <u>member configured</u> for forming a vacuum-tight seal between said first electrode and said second electrode <u>when said second electrode is moved to said first position</u>, said separating [[ring]] <u>member defining a sidewall between said first electrode and said second electrode</u>, <u>said first electrode adapted to support the substrate in a processing region between said first electrode and said second electrode for plasma processing, and said separating [[ring]] <u>member comprising</u> a dielectric material for electrically isolating said first electrode from said second electrode;</u>
- a process gas port for introducing a process gas to said processing region; and a vacuum port for evacuating said processing region to a pressure suitable for generating the plasma from the process gas in said processing region.
- 2. (Original) The apparatus of claim 1 further comprising:
- a vacuum manifold coupled with said vacuum port, said vacuum manifold being electrically isolated from said first electrode and said second electrode.
- 3. (Original) The apparatus of claim 2 wherein said vacuum manifold includes an enclosed volume proximate to said vacuum port and further comprising:

an insert of an electrically insulating material positioned inside said enclosed volume, said insert including a first plurality of passages coupling said vacuum manifold with said vacuum port.

- 4. (Original) The apparatus of claim 3 wherein said vacuum port is defined by a second plurality of passages extending through said first electrode and registered with said first plurality of passages.
- 5. (Original) The apparatus of claim 1 further comprising:

a vacuum pump coupled with said vacuum port and operative for evacuating said processing region to said pressure suitable for generating the plasma from the process gas in said processing region.

- 6. (Original) The apparatus of claim 1 further comprising:
- a process gas supply coupled with said process gas port for introducing the process gas to said processing region.
- 7. (Original) The apparatus of claim 1 wherein said second electrode includes a plurality of openings arranged in a pattern effective for communicating process gas from said process gas port to said processing region.
- 8. (Original) The apparatus of claim 1 further comprising:
- a substrate holder positioned inside said processing region and configured to support the substrate on said first electrode.
- 9. (Original) The apparatus of claim 8 wherein said substrate holder is electrically coupled with said first electrode.
- 10. (Original) The apparatus of claim 1 further comprising:

an electrically-conductive enclosure surrounding said separating ring, said first electrode, and said second electrode, said first electrode and said second electrode each separated from said conductive enclosure by an air gap.

- 11. (Original) The apparatus of claim 10 wherein said enclosure includes a base and a lid movable relative to said lid between opened and closed positions for accessing said processing region, said lid carrying said first electrode for movement relative to said base.
- 12. (Currently Amended) The apparatus of claim 10 further comprising a coolant port in said lid <u>configured</u> for supplying a flow of a coolant fluid to said air gap for cooling said first electrode and said second electrode.
- 13. (Original) The apparatus of claim 1 wherein said first electrode includes said vacuum port and said second electrode includes said process gas port.
- 14. (Original) The apparatus of claim 13 wherein said second electrode includes a plurality of gas openings coupled with said process gas port, said plurality of gas openings positioned in said second electrode to distribute process gas across a confronting surface of the substrate.
- 15. (Currently Amended) An apparatus for plasma processing a plurality of substrates, <u>the apparatus</u> comprising:
 - a first electrode;
- a second electrode positioned with a spaced apart relationship relative to said first electrode;
- a third electrode positioned between said first electrode and said second electrode; a first <u>tubular</u> separating [[ring]] <u>member configured</u> for forming a vacuum-tight seal between said first electrode and said third electrode and defining a first processing region between said first electrode and said third electrode, said first electrode <u>adapted configured</u> to support one of the plurality of substrates in said first processing region for plasma processing, and said first separating ring comprising a dielectric material for electrically isolating said first electrode from said third electrode;

a second <u>tubular</u> separating [[ring]] <u>member configured</u> for forming a vacuumtight seal between said second electrode and said third electrode to define a second processing region between said second electrode and said third electrode, said third electrode adapted <u>configured</u> to support one of the plurality of substrates in said second processing region for plasma processing, and said second separating ring comprising a dielectric material for electrically isolating said second electrode from said third electrode;

at least one process gas port for introducing a process gas to said first processing region and second processing region; and

a vacuum port for evacuating said processing region to a pressure suitable for generating the plasma from the process gas in said first processing region and said second processing region.

- 16. (Original) The apparatus of claim 15 wherein said vacuum port is defined in said second electrode.
- 17. (Currently Amended) The apparatus of claim 16 wherein said first electrode includes a first process gas port <u>configured</u> for introducing the process gas to said first processing region and said third electrode includes a second process gas port <u>configured</u> for introducing the process gas to said second processing region.